P-Channel Enhancement Mode Field Effect Transistor

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Product Summary

• V_{DS}	-60 V
• I_D	-100 A
• $R_{DS(ON)}$(at V_{GS}=-10V)	8.8mΩ
• $R_{DS(ON)}$(at V_{GS}=-6V)	10mΩ
• 100% EAS Tested1	
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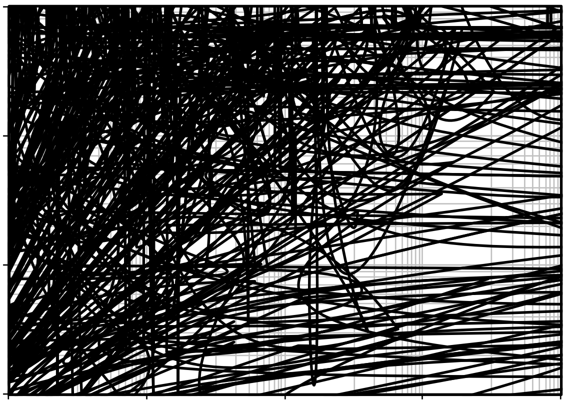
■ Electrical Characteristics (T$_J$=25 unless otherwise noted)

Parameter	Symbol	[redacted]	Min	Typ	Max



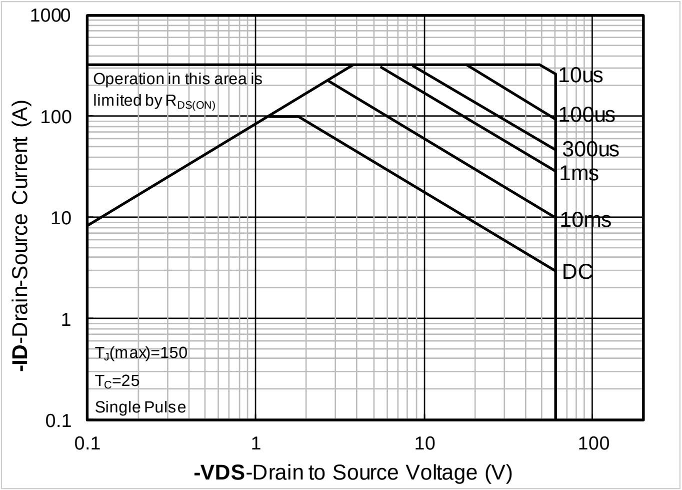


Figure 13. Maximum Transient Thermal Impedance

Figure

■TO-263-HY Package information

SYM	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes wu Ya n ce ThsElncEBTf3(ti28(c))6(a)-3(ti)7(o)-39 n o th n poecTs2-108(d)-5(i)-47121(p)lgye7(o)d39 n Elnrehn